

# **Jerzy Kanicki**

## **Presentations at Professional Meetings, University and Industry**

**1980-2011**

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**Invited Conference Presentations**

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## INVITED SHORT COURSES, TAUTORIALS AND LECTURES

1. **Int. Conf. on “Science and Technology of Display Phosphors,** “*Organic Polymer Light-Emitting Devices and Displays on Plastic Flexible Substrates,*” J. Kanicki, Y. He, Y. Hong, Z. He, Z. Hong and A. Badano, November, 6-8, 2000, San Diego, CA.
2. **Society for Information Display, 2005 Int. Symposium One Day Seminar Lectures,** “*Organic Field -Effect Transistors for Flat Panel Displays,*” J. Kanicki, E. Cagin, M. Hamilton, H. Lee and P. Shea, May 23, 2005, Boston, MA.
3. **Society for Information Display, 26<sup>th</sup> International Display Research Conference,** “*Organic Field-Effect Transistors and Electronics,*” J. Kanicki, P.B. Shea and H. Lee, September 18, 2006, Kent, OH.
4. **Corning Display Workshop,** “*Organic and Oxide Semiconductor Thin-Film Transistors for Flat Panel Displays,*” J. Kanicki and P. Shea, October 26, 2006, Corning, NY.
5. **SID (Society for Information Display), 2008 Vehicles and Photons Symposium,** “*Amorphous Metal Oxide Thin-Film Transistors for Flexible Displays,*” J. Kanicki October 16-17, 2008, Dearborn, MI.
6. **SID (Society for Information Display), 2010 Vehicles and Photons Symposium,** “*Flexible Displays,*” J. Kanicki, October 21 – 22, 2010, Dearborn, MI.
7. Presentation to MITI Committee on “Flexible Displays” sponsored by **Ministry of International Trade and Industry (MITI)**, , “*Flexible Displays – US Status & Trend,*” J. Kanicki, January 20, 2010, Fukuoka, Japan
8. **SID (Society for Information Display), 2011 Vehicles and Photons Symposium,** “*a-InGaZnO TFT for Future Active-Matrix Displays,*”, J. Kanicki, October 20 – 21, 2011, Dearborn, MI

## INVITED CONFERENCE PRESENTATIONS

1. **International Conference on Conducting Polymers and the International CNRS Colloquium on the Physics and Chemistry of Synthetic and Organic Metals,** “*Review of Conductor – Polymeric Semiconductor Solar Cells,*” J. Kanicki, December 14-18, 1982, Les Arcs, France.
2. **1987 Materials Research Society Spring Meeting,** “*Metal/Hydrogenated Amorphous Silicon Interfaces,*” J. Kanicki, April 21-25, 1987, Palo Alto, CA.

3. **1988 American Physical Society March Meeting**, "Material and Interface Issues in Hydrogenated Amorphous Silicon Thin-Film Transistor for Microelectronics," J. Kanicki, March 21-25, 1988, New Orleans, LA.
4. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, "Metal/Hydrogenated Amorphous Silicon Interfaces," J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.
5. **1989 Japan Society of Applied Physics Spring Meeting**, "Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films," J. Kanicki, April 1-4, 1989, Chiba, Japan.
6. **179th Electrochemical Society Meeting**, "A Magnetic Resonance Investigation of Silicon Dangling Bonds in Silicon Nitride," W.L. Warren, P.M. Lenahan, F.C. Rong, E.H. Poindexter and J. Kanicki, May 5-10, 1991, Washington DC.
7. **15th Int. Conf. on Amorphous Semiconductors: Science and Technology**, "Defects in Amorphous Hydrogenated Silicon Nitride Films," J. Kanicki and W.L. Warren, September 12-14, 1993, Cambridge, U.K.
8. **Active-Matrix Liquid Crystal Displays Symposium**, "Amorphous Hydrogenated Silicon Thin Film Transistors: Physics and Technology," J. Kanicki, October 21-22, 1993, Bethlehem, PA,
9. **1993 Int. Semiconductor Device Research Symposium**, "Bias Stress-Induced Instabilities in Amorphous Silicon Thin Film Transistors: Charge Trapping or Carrier-Induced Defect Creation," J. Kanicki and F.R. Libsch, December 1-3, 1993, Charlottesville, VA.
10. **1994 European Materials Society Spring Meeting**, "a-Si:H TFT's Instability and Lifetime Requirements for AMLCD's," F.R. Libsch and J. Kanicki, May 24-27, 1994, Strasbourg, France.
11. **1995 American Vacuum Society Meeting**, "Thin Film Transistor-Liquid Crystal Displays in the Year 2000," J. Kanicki, March 2, 1995.
12. **1995 American Chemical Society Fall Scientific Meeting** on Materials for Emerging Technologies, "Thin-Film Transistor Liquid-Crystal Displays for the Year 2000," J. Kanicki, November 4, 1995, Midland, MI.
13. **1996 Materials Research Society Spring Meeting**, "Flat Panel Display Materials," J. Kanicki, April 8-12, 1996, San Francisco, CA.

14. **26<sup>th</sup> European Solid-State Device Research Conf., "High-Performance a-Si:H TFT for Large Area AMLCDs,"** C.-Y. Chen and J. Kanicki, September 9-11, 1996, Bologna, Italy.
15. **1996 Int. Active-Matrix Workshop, "Electrical Performance and Instability of High Field Effect Mobility a-Si:H TFTs Fabricated from High Deposition Rate PECVD Materials,"** C.-Y. Chen and J. Kanicki, September 30, 1996, Birmingham, U.K.
16. **Mardi Gras Conf. '97 on Multiscale Phenomena in Science and Engineering, "Materials for Flat Panel Displays,"** J. Kanicki, February 7-9, 1997, Baton Rouge, LA.
17. **Electronic Display Forum '97, "The Challenges of Research and Development in Universities on Flat Panel Displays and the Active Relationship between Academia and Industry,"** J. Kanicki, April 16-18, 1997, Pacifico Yokohama, Japan.
18. **1997 Int. Workshop on Active-Matrix Liquid-Crystal Displays, "Gated-Four-Probe a-Si:H TFT Structure: a New Technique to Measure the Intrinsic Performance of a-Si:H TFT,"** C.-S. Chiang, C.-Y. Chen and J. Kanicki, September 11-12, 1997, Tokyo, Japan.
19. **1998 SPIE (The International Society for Optical Engineering) Conf. on Display Technologies II, "Planarization Technology of a-Si:H TFTs for AM-LCDs,"** J.-H. Lan and J. Kanicki, July 9-11, 1998, Taipei, Taiwan.
20. **Photonics China '98, "Viewing-Angle Improvement with Compensation Films for LCDs,"** G. Xu, A. Abileah, M. Jones, R. Brinkley, S.V. Thomsen, S. Gong and J. Kanicki, September 16-17, 1998, China.
21. **18<sup>th</sup> Int. Display Res. Conf. (Asia Display '98), "Top-Gate a-Si:H TFT-LCD Technology: Past, Present and Future,"** J. Kanicki, S. Martin and Y. Ugai, September 28 – October 1, 1998, Seoul, Korea.
22. **The 6<sup>th</sup> International Conf. on the Science and Technology of Display Phosphors, Society for Information Display, "Organic Polymer Light-Emitting Devices and Displays on Plastic Flexible Substrate,"** J. Kanicki, Y. He, Y. Hong, Z. He, Z. Hong and A. Badano, November 6-8, 2000, San Diego, CA.
23. **2001 IS&T/SPIE 13<sup>th</sup> Int. Symposium on Electronic Imaging – Science and Technology, "a-Si:H Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays,"** J. Kanicki, Y. He and R. Hatori, January 21-26, 2001, San Jose, CA.

24. **2001 Materials Research Society Spring Meeting**, "Amorphous Silicon Thin Film Transistor Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays," J. Kanicki and J. Kim, April 16-20, 2001, San Francisco, CA.
25. **Asia Display/International Display Workshops'01**, "Amorphous Silicon Thin-Film Transistors Based Active-Matrix Organic Light-Emitting Displays," J. Kanicki, J.-H. Kim, J.Y. Nahm, Y. He and R. Hattori, October 10-19, 2001, Nagoya, Japan.
26. **2001 Int. Conf. on the Science and Technology of Emissive Displays and Lighting**, "Organic Polymer Light Emitting Devices on Plastic Substrates," J. Kanicki, Y. Hong, Z. He, S. Lee, and A. Badano, November 12 14, 2001, San Diego, CA.
27. **American Chemical Society – 2002 Great Lakes Regional Meeting**, "Organic Polymer Light-Emitting Devices on Plastic Substrates for Active-Matrix Organic Polymer Light-Emitting Displays," J. Kanicki, Y. Hong, and S. Lee, June 2-4, 2002, Minneapolis, MN.
28. **2002 International Workshop on Active-Matrix Liquid-Crystal Displays**, "Three a-Si:H TFT Pixel Electrode Circuit for AM-OLEDs," J. Kanicki and J.-H. Kim, July 10-12, 2002, Tokyo, Japan.
29. **2003 Materials Research Society Spring Meeting**, "200 dpi a-Si:H TFT Active Matrix Organic Polymer Light-Emitting Displays," J. Kanicki and Y. Hong, April 21-25, 2003, San Francisco, CA.
30. **2003 Flat Panel Display International**, "a-Si:H TFTs Active-Matrix Organic Polymer Light-Emitting Displays," J. Kanicki, October 29-31, 2003, Pacifico Yokohama, Japan.
31. **24<sup>th</sup> Int. Display Research Conference and 4<sup>th</sup> Int. Meeting on Inf. Display**, "Organic Polymer Light-Emitting Devices on a Flexible Plastic Substrate," J. Kanicki, S.J. Lee, Y. Hong and C.C. Su, August 23-27, 2004, Daegu, Korea.
32. **2005 Int. Conf. on Solid-State Devices and Materials**, "Tetrabenzoporphyrin Organic Semiconductors for Flexible Organic Thin Film Transistors and Circuits," P. Shea, J. Kanicki and N. Ono, September 13-15, 2005, Kobe, Japan.
33. **Society of Information Display, 2005 Vehicle Display Symposium**, "Optoelectric Properties of a-Si:H TFTs 100 dpi Active-Matrix Polymer Light-Emitting Display," J. Kanicki, October 6-7, 2005, Dearborn, MI.
34. **2006 Materials Research Society Spring Meeting, Symposium on "Materials for Next Generation Display Systems,"** "Inorganic Semiconductor Thin-Film

- Transistors for Flat Panel Displays,”* J. Kanicki, H. Lee, A. Kuo, J. Siddiqui, C. Chen and J. Phillips, April 18-20, 2006, San Francisco, CA.
35. **13<sup>th</sup> Int. Workshop on Active-Matrix Flat Panel Displays and Devices – TFT Technologies and Related Materials,** “*Thermal and Electrical Instability of Amorphous Silicon Thin-Film Transistors for AM-FPDs,*” A. Kuo and J. Kanicki, July 5-7, 2006, Tokyo, Japan.
36. **IDMC’07 (International Display Manufacturing Conference & FPD Expo),** “*Novel Pixel Electrode Circuits and a-Si:H TFT Structures for AM-OLEDs,*” H. Lee, J.S. Yoo, C.-D. Kim, I. Kang and J. Kanicki, July 3-6, 2007, Taipei International Convention Center, Taiwan.
37. **International Workshop on Transparent Amorphous Oxide Semiconductors TACOS 2010,** “*A-IGZO Density of States: Photo-Field Effect and Temperature Dependence Studies,*” T.C. Fung, C. Chen and J. Kanicki, January 25-26, 2010, Tokyo Institute of Technology, Yokohama, Japan.
38. **6<sup>th</sup> International Thin – Film Transistor Conference,** “*Electrical Stability of Advanced a-Si:H TFT Structures,*” G. Yoo, H. Lee and J. Kanicki, January 28 – 29, 2010, Egret, Himeji, Japan.
- INVITED UNIVERSITY AND INDUSTRIAL SEMINARS**
1. **Journees d'Etudes d'Electrochimie,** “*Photovoltaisme des Jonctions Metal-Semiconducteur Organique,*” J. Kanicki and J. M. Dohan, 27-29 April, 1981, Macon, France.
  2. **N.F.W.O.-F.N.R.S. Contact Group Molecular Photochemistry,** “*Optical, Electrical and Photovoltaic Properties of trans-Polyacetylene,*” Boue, J.M. Dohan, P. Fedorko, J. Kanicki and E. Vander Donckt, March 1982, Brussels, Belgium.
  3. **Chronar Corp.,** “Schottky Barrier Polyacetylene Solar Cells.” J. Kanicki, Princeton, September 23, 1983, NJ.
  4. **Xerox Webster Research Center,** “*Homogeneous Chemical Vapor and Plasma Deposition in Amorphous Silicon Technology,*” J. Kanicki and B.A. Scott, November 9, 1983, Rochester, NY.
  5. **Exxon Corp.,** “*HOMOCVD Deposited Films and Their Application in Photovoltaic Devices.*” J. Kanicki and B.A. Scott, Linden, November 15, 1983, NJ.

6. **IBM Thomas J. Watson Research Center**, "Metal/a-Si:H Contacts," J. Kanicki, Yorktown Heights, February 17, 1984, NY.
7. **1984 New York State University Spring Seminar Series**, "Metal-Polyacetylene Schottky Barrier Diodes," J. Kanicki, April 13, 1984, Buffalo, NY.
8. **TFT-LCD's IBM Program Planning Meeting**, "Review on TFT Processing and Current Status," J. Kanicki, August 28-29, 1984, Kingston, NY.
9. **IBM Eastview Research Laboratory**, "Metal/Amorphous Silicon Contacts," J. Kanicki and D.B. Bullock, October 1985, Eastview, NY.
10. **IBM Eastview Research Laboratory**, "Materials and Metallization Requirements for Active-Matrix Devices," J. Kanicki, July 7, 1986, Eastview, NY.
11. **IBM Almaden Research Center**, "Comparative Study of PECVD Nitride Films," J. Kanicki, October 27, 1986, Almaden, CA.
12. **United Technologies Research Center**, "Material Analysis of Silicon Nitride Films Deposited in Various PECVD Systems," J. Kanicki, November 12, 1986, East Hartford, CT.
13. **Pennsylvania State University**, "Metal/Hydrogenated a-Si:H Contacts," J. Kanicki, November 19, 1986, University Park, PA.
14. **1987 Amorphous Silicon Subcontractors' Review Meeting**, "The Contact Issue in the Hydrogenated Amorphous Silicon Technology," J. Kanicki, January 26-27, 1987, Palo Alto, CA.
15. **Xerox Palo Alto Research Center**, "Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various PECVD Systems," J. Kanicki, November 2, 1987, Palo Alto, CA.
16. **University of North Carolina**, "Metal/Hydrogenated Amorphous Silicon Interfaces," J. Kanicki, November 17, 1987, Chapel Hill, NC.
17. **North American Philips Corporation**, "The Contacts Issues in the Hydrogenated Amorphous Silicon Thin-Film Transistor Technology," J. Kanicki, November 24, 1987, Briarcliff Manor, NY.
18. **T. J. Watson Research Laboratory**, "Comparative Study of PECVD Nitride Films," J. Kanicki, December 4, 1987, Yorktown Heights, NY.
19. **IBM East Fishkill Seminar Series**, "Microcrystalline Silicon: Material Properties and Applications," J. Kanicki, April 28, 1988, East Fishkill, NY.

20. **Seminar Series of Institute of Energy Conversion**, "University of Delaware Material and Interface Issues in Hydrogenated Amorphous Silicon Thin Film Transistors," J. Kanicki, May 19, 1988, Newark, DE.
21. **Trench Workshop III - Trench Fill**, "Hydrogenated Amorphous Silicon: Preparation, Properties and Applications," J. Kanicki, IBM East Fishkill, June 1-3, 1988, NY.
22. **Seminar Series of Sherman Fairchild Center**, "Lehigh University Material and Interface Issues in Hydrogenated Amorphous Silicon Thin Film Transistors," J. Kanicki, June 22, 1988, Bethlehem, PA.
23. **IBM Yamato Development Laboratory**, "Highly Conductive P-doped Microcrystalline Silicon," J. Kanicki, July 1988, Japan.
24. **TFT/LCD IBM Review Meeting**, "Microcrystalline TFT's Contacts," J. Kanicki, March 16-17, 1989, Eastview, NY.
25. **IBM Yamato Laboratory**, "Properties of Undoped and Phosphorous Doped Microcrystalline Silicon Thin Films," J. Kanicki, April 4, 1989, Yamato, Japan.
26. **IBM Yamato Laboratory**, "Properties of N-rich Amorphous Silicon Nitride Thin Films," J. Kanicki, April 5, 1989, Yamato, Japan.
27. **Toshiba Research and Development Center**, "Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films," J. Kanicki, April 6, 1989, Kawasaki, Japan.
28. **Matsushita Electric Central Center Research Laboratory**, "Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films," J. Kanicki, April 7, 1989, Osaka, Japan.
29. **Tokyo Institute of Technology**, "Properties of Undoped and Phosphorous Doped Microcrystalline Silicon Thin Films," J. Kanicki, April 10, 1989, Tokyo, Japan.
30. **Eectrotechnical Laboratory Center**, "Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films," J. Kanicki, April 11, 1989, Tsukuba, Japan.
31. **IBM Research Seminar Series**, "Amorphous Silicon Thin Film Transistor Technology," J. Kanicki, Yorktown Heights, May 19, 1989, NY.
32. **University "La Sapienza" of Rome**, "Properties of Dielectric Films Deposited by Plasma-Enhanced Chemical Vapor Deposition," J. Kanicki, September 22, 1989, Rome, Italy.

33. **Institute of Electronic of the Solid State**, "Materials and Interface Issues in Hydrogenated Amorphous Silicon Thin Film Transistor," J. Kanicki, September 25, 1989, Rome, Italy.
34. **Interuniversities Micro-Electronic Center**, "Observation of the Silicon Nitride Interface Properties on Crystalline and Amorphous Silicon Interface," J. Kanicki, October 3, 1989, Leuven, Belgium.
35. **Institute of Thin Film and Ion Technology**, "Interface States at the Silicon Nitride/Amorphous and Crystalline Silicon Interfaces," J. Kanicki, October 9, 1989, Julich, Germany.
36. **1989 IBM ASTL Symposium**, "How to Control and Improve Polysilicon Emitter," J. Tien, P. Ronsheim, T. Walker, T. Smutek, D. E. Kotecki, S.J. Jeng, J. Kanicki, C.C. Parks, W. Rausch, E. Grabbe, K. Seshan, L. Prabhu, and B.W. Hicks, November 7-9, 1989, East Fishkill, NY.
37. **1989 IBM ASTL Symposium**, "Properties of in-Situ Phosphorous-doped Hydrogenated Microcrystalline Silicon and its Application as a Wide-Gap Emitter Material," D. E. Kotecki, S.J. Jeng, J. Kanicki, C.C. Parks, W. Rausch, K Seshan and J. Tien, November 7-9, 1989, East Fishkill, NY.
38. **IBM Eastview Laboratory**, "Light-Induced ESR in Nitrogen-Rich Gate-Quality Amorphous Silicon Nitride Films," M S. Crowder, E.D. Tober, J. Kanicki and D. Jousse, December 1989, Eastview, NY.
39. **IBM Eastview Laboratory**, "Stretched-Exponential Illumination Time Dependence of Positive Charge and Spin Generation by Subbandgap UV-light in Amorphous Silicon Nitride Films," J. Kanicki, M. Sankaran, A. Gelatos, M.S. Crowder, E.T. Tober, March 5, 1990, Eastview, NY.
40. **IBM Eastview Laboratory**, "Performance of the 55 nm Amorphous Silicon TFT" J. Kanicki, J. Griffith, and R. Polastre, March 12, 1990, Eastview, NY.
41. **IBM Research Division Seminar Series**, "Structure of Trapping Centers in Silicon Nitride," P.M. Lenahan, D.T. Krick, W.L. Warren, S. Curry and J. Kanicki, April 6, 1990, Eastview, NY.
42. **1990 Spring Masterslice Seminar Series**, "Hydrogenated Amorphous Silicon Thin Film Transistors: Physics, Properties and Applications," J. Kanicki, May 1, 1990, East Fishkill, NY.
43. **IBM Department 600 Accomplishment Review Meeting**, "Nature of Defects and Kinetics of Trapping in N-rich Amorphous Silicon Nitride," J. Kanicki, November 26, 1990, Eastview, NY.

44. **1990 IBM ASTL Symposium**, "Properties, Structure and Application of *in-Situ Phosphorous Doped Hydrogenated Microcrystalline Silicon*," S.T. Jeng, D.E. Kotecki, J. Kanicki, C.C. Parks, J. Tien and L. Prabhu, December 1990. East Fishkill, NY.
45. **The Pennsylvania Surface Science Workshop**, "Polysilicon Film/Gate Oxide Interface of Polycrystalline Silicon Thin Film Transistors," J.H. Jung, S. Lin, M. Hatalis and J. Kanicki, May 15, 1991, Bethlehem, PA.
46. **Computer Science and Electrical Engineering Seminar Series, Lehigh University**, "Hydrogenated Amorphous Silicon Thin Film Transistors for Flat Panel Displays," J. Kanicki, October 9, 1991, Bethlehem, PA.
47. **Princeton University, EMD Seminar Series**, "Thin Film Transistors: Physics, Properties and Applications," J. Kanicki, April 5, 1993, Princeton, NJ.
48. **IBM Entry System Technologies Laboratory Accomplishments Meeting**, "a-Si:H TFT Electrical Stability," F. Libsch and J. Kanicki, May 12, 1993, Eastview, NY.
49. **AT&T Laboratories, Flat Panel Display Seminar Series**, "Low Temperature Materials for Thin Film Transistors," J. Kanicki, December 14, 1993, Murray Hill, NJ.
50. **Center for Display Technology & Manufacturing, University of Michigan**, "Thin Film Transistors for Liquid Crystal Flat Panel Displays," J. Kanicki, December 17, 1993, Ann Arbor, MI.
51. **Toshiba Corp.**, "UV-Light Induced Changes in Polyimide LC Alignment Films," J. Kanicki, August 31, 1995, Kawasaki, Japan.
52. **IBM Japan Ltd.**, "Simulation of the High Performance a-Si:H TFT for High Definition LCDs," J. Kanicki, August 31, 1995, Yamamoto, Japan.
53. **Sharp Corp.**, "a-Si:H TFTs," J. Kanicki, August 28, 1995, Osaka, Japan.
54. **NEC Corp.**, "Simulation of the High Performance a-Si:H TFT for High Definition LCDs," J. Kanicki, August 30, 1995, Tokyo, Japan.
55. **Hosiden Corp.**, "Simulation of the High Performance a-Si:H TFT for High Definition LCDs," J. Kanicki, August 29, 1995, Kobe, Japan.
56. **DTI Inc.**, "Simulation of the High Performance a-Si:H TFT for High Definition LCDs," J. Kanicki, August 29, 1995, Tokyo, Japan.
57. **Hitachi Ltd.**, "a-Si:H TFTs," J. Kanicki, August 30, 1995, Tokyo, Japan.

58. **Annual Meeting of the Society of Motion Picture and Television Engineers**, “*Thin-Film Transistor Liquid-Crystal Displays for Year 2000*,” J. Kanicki, February 13, 1996, Southfield, MI.
59. **Dow Chemical Corp.**, “*Planarization of a-Si:H TFTs*,” J. Kanicki, November 18-19, 1997, Midland, MI.
60. **Physics Seminar at Ford Corp.**, “*Reflective and OLED Based Flat Panel Displays*,” J. Kanicki, November 5, 1998, Dearborn, MI.
61. **Dow Corning Corp.**, “*Spin-coated Flowable Oxide for AMLCD*,” J. Kim and J. Kanicki, January 29, 1999, Midland, MI.
62. **Kodak Research Laboratories**, “*Amorphous Silicon Based AM-OLEDs*,” J. Kanicki, October 16, 2000, Rochester, N.Y.
63. **Optical Society of America**, “*Organic Polymer Light-Emitting Devices and Displays*,” J. Kanicki, October 17, 2000, Ann Arbor, MI.
64. **Hope College**, “*Organic Polymer Light-Emitting Devices and Displays*,” J. Kanicki, January 12, 2001, Holland, MI.
65. **Dow Corning Corp.**, “*Organic Polymer Light-Emitting Devices on Plastic Substrates*,” J. Kanicki, S.J. Lee and Y. Hong, February 2004, Midland, MI.
66. **LG. Phillips LCD**, “*AM-PLEDs Based on a-Si:H TFTs*,” J. Kanicki, August 30, 2004, Anyang-Shi, Gyeonggi-do, Korea.
67. **LG. Phillips LCD**, “*a-Si:H TFT AM-PLEDs*,” J. Kanicki, August 27, 2004, Kumi-city, Kyunbuk, Korea.
68. **Samsung Advanced Institute of Technology**, “*Organic Polymer Light-Emitting Devices on Flexible Plastic Substrate*,” J. Kanicki, Y. Hong, S.J. Lee and H. Lee, August 31, 2004, Yongin-si, Gyeonggi-do, Korea.
69. **Samsung SDI**, “*a-Si:H TFT Back Plane for AM-OLEDs*,” J. Kanicki, J. Kim and Y. Hong, August 31, 2004, Yongin-si, Gyeonggi-do, Korea.
70. **Samsung Electronics Co., LTD**, “*a-Si:H TFT AM-PLEDs*,” J. Kanicki, J. Kim and Y. Hong, September 1, 2004, Yongin-si, Gyeonggi-do, Korea.
71. **Air Force Research Laboratory**, “*Organic Polymer Devices on Flexible Plastic Substrates*,” J. Kanicki, Y. Hong, S.J. Lee and H. Lee, November 19, 2004, Wright-Paterson, AFB, OH.

72. **Matsushita Electric Industrial Co., Ltd**, “*Tetrabenzoporphyrin-Based Filed-Effect Transistors*; & “*White Light-Emitting Device on Flexible Plastic Substrates*,” P. Shea, J. Kanicki and H. Lee, September 13, 2005, Osaka, Japan.
73. **Sanyo Electric Co., Ltd**, “*Organic Polymer Thin-Film Transistors*,” J. Kanicki, P. Shea and M. Hamilton, September 16, 2005, Osaka, Japan.
74. **Ehime University**, “*Tetrabenzoporphyrin-Based Field-Effect Transistors*,” P.B. Shea and J. Kanicki, September 17, 2005, Matsuyama, Japan.
75. **Dow Corning Corp. Seminar Series**, “*Organic Polymer Light-Emitting Devices on Plastic Substrate*,” J. Kanicki, Y. Hong and H. Lee, February 2, 2006, Midland, MI.
76. **University of Tokyo**, “*Electronic Properties of Porphyrin-Based Organic Transistors*,” J. Kanicki and P. Shea, July 7, 2006, Tokyo, Japan.
77. **Ehime University**, “*Solution Processed Organic Semiconductors for Flexible Organic Thin Film Transistors and Circuits*,” J. Kanicki, July 10, 2006, Matsuyama, Japan.
78. **3M Corp. Seminar Series**, “*White-Light and Thin-Film Transistors for Future Flat Panel Displays*,” J. Kanicki, October 20, 2006, Minneapolis-St. Paul, MN.
79. **Toppan Printing Co.**, “*Organic Semiconductor Thin-Film Transistors for Flat Panel Displays*,” J. Kanicki and P.B. Shea, July 2, 2007, Saitama, Japan.
80. **Tokyo Institute of Technology**, “*a-Si:H TFTs versus a-IGZO TFTs*,” J. Kanicki, July 2, 2007, Tokyo, Japan.
81. **Fuji Electric Advanced Technology Co., Ltd.**, “*Organic Semiconductor Thin-Film Transistors for Flat Panel Displays*,” J. Kanicki and P.B. Shea, July 3, 2007, Tokyo, Japan.
82. **Canon Inc.**, Canon Research Center, “*Advanced a-Si:H TFTs for Flat Panel Displays*,” J. Kanicki, P. Ahn and A. Kuo, July 3, 2007, Tokyo, Japan.
83. **Canon Inc.**, Canon Research Center, “*A-In-Ga-Zn-O for Future Flat Panel Displays*,” J. Kanicki, C. Chen and R. Fung, January 21, 2010, Tokyo, Japan.
84. **Sharp Corp.**, Advanced Technology Development Center, “*2D Numerical Simulation, BTS, and CTS of Amorphous In-Ga-Zn-O Thin Film Transistors*,” J. Kanicki, January 26, 2010, Tenri, Nara, Japan.
85. **Qualcomm Inc.**, Qualcomm Research Center, “*Amorphous In-Ga-Zn-O Thin Film Transistor for Future Optoelectronics*,” J. Kanicki and T.-C. Fung, July 28, 2010, San Diego, CA.

## INVITED PANELIST

1. **2005 Int. Conf. on Solid-State Devices and Materials (SSDM 2005),** "Flexible Electronics – Is it Real?" J. Kanicki, September 14, 2005, Kobe, Japan.

## CONTRIBUTED CONFERENCE PRESENTATIONS

1. **VIII IUPAC Symposium on Photochemistry,** "The poly-2-Vinylpridine Iodine Complex- $\text{SnO}_2$  System Under Near U.V. and Visible Light Irradiation," B. Noirhomme, J. Kanicki and E. Vander Donckt, July 13-19, 1980, Seefeld, Austria.
2. **International Conference on Low Dimensional Synthetic Metals,** "Relation between Optical and Electrical Properties of the trans- $\text{CH}_x$ -Iodine Complex: Variable Range Hopping," J. Kanicki, August 10-15, 1980, Helsingor, Denmark.
3. **Congres de la Societe Francaise de Physique,** "Relation Entre les Proprietes Optique et Electriques du Polyacetylene Dope par les Halogenes.," J. Kanicki, E. Vander Donckt et S. Boue, June 29-July 4, 1981, Clermont-Ferrand, France.
4. **International Conference on Low-Dimensional Conductors,** "Photovoltaic and Rectification Properties of In / trans- $\text{CH}_x$  Electrode +502 Schottky-Barrier Cells," J. Kanicki, S. Boue and E. Vander Donckt, August, 10-14 1981, Boulder, CO.
5. **2nd General Conference of the Condensed Matter Division of the European Physical Society,** "Contact Properties Between Undoped trans-Polyacetylene and Metals," J. Kanicki, P. Fedorko, S. Boue and E. Vander Donckt, March 22-25, 1982, Manchester, U. K.
6. **Symposium on Conducting Polymers at the American Chemical Society Meeting,** "Organic Photovoltaic Materials," J. Kanicki, May 10-14, 1982, Stresa, Italy.
7. **Symposium on Order in Polymeric Materials: Implications for Electronic, Metals-Magnetic, and Optical Phenomena,** "Metals Polyacetylene Schottky Barrier Diodes," J. Kanicki, August 25-26, 1983, GTE Laboratories, Waltham, MA.
8. **4th EC Photovoltaic Solar Energy Conference,** "Organic Photovoltaic Materials," J. Kanicki, May 10-14, 1982, Stresa, Italy.

9. **64th Meeting of the Electrochemical Society**, "Hydrogenated Amorphous Silicon Schottky Barrier Structures Prepared by Homogeneous Chemical Vapor Deposition," J. Kanicki, J.F. Nijs, B.A. Scott, R.M. Plecenick and B.S. Meyerson, October 9-14, 1983, Washington, D.C.
10. **Fifth EC Photovoltaic Solar Energy Conference**, "Amorphous Hydrogenated Silicon Solar Cells with the Homogeneous CVD Technique," F. Nijs, J. Kanicki, B.A. Scott, R.M. Plecenick and B.S. Meyerson, October 17-21, 1983, Kavouri Bay Athens, Greece.
11. **International Topical Conference on Transport and Defects in Amorphous Semiconductors**, "Transport Properties and Defect States of a-Si:H Grown by HOMOCVD," J. Kanicki, C.M. Ransom, W. Bauhofer, T.I. Chappell and B.A. Scott, March 22-24, 1984, Bloomfield Hills, MI.
12. **International Conference on Optical Effects in Solids**, "Photoconductivity of Intrinsic and Doped a-Si:H from 0.1 to 0.9 eV," T. Inushima, M.H. Brodsky, J. Kanicki and R.J. Serino, August 1-4, 1984, Salt Lake City, UT.
13. **International Conference on the Physics of Semiconductors**, "Schottky Barrier Formation at Metal-Hydrogenated Amorphous Silicon Interfaces," J. Kanicki, M. Osama Aboelfotoh and W. Bauhofer, April 6-10, 1984, San Francisco, CA.
14. **1985 Materials Research Society Meeting**, "Minority Carrier Injection and Series Resistance Effects in Hydrogenated Amorphous Silicon Schottky Diode," J. Kanicki, April 15-18, 1985, San Francisco, CA.
15. **167th Electrochemical Society Meeting**, "Contact Properties of Metal Polyacetylene Interfaces," J. Kanicki, May 12-17, 1985, Toronto, Canada.
16. **11th International Conference on Amorphous and Liquid Semiconductors**, "Optical, Electrical and Contact Properties of HOMOCVD a-Si:H Films," J. Kanicki, B.A. Scott, T. Inushima and M.H. Brodsky, September 2-6, 1985, Rome, Italy.
17. **1986 Materials Research Society Meeting**, "Chemical and Mechanical Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various Systems," J. Kanicki and N. Voke, April 15-19, 1986, Palo Alto, CA.
18. **1986 Materials Research Society Meeting**, "Optical and Electrical Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various Systems," J. Kanicki and N. Voke, April 15-19, 1986, Palo Alto, CA.

19. **1986 Materials Research Society Meeting**, "Ohmic and Quasi-Ohmic Contacts to Hydrogenated Amorphous Silicon Thin Films," J. Kanicki and D. Bullock, April 15-19, 1986, Palo Alto, CA.
20. **1986 Metallurgical Society Northeast Regional Meeting**, "Metallization to Hydrogenated Amorphous Silicon Thin Films," J. Kanicki, May 1-2, 1986, Murray Hill, NJ.
21. **170th Electrochemical Society Meeting**, "Comparative Study of PECVD Nitride Films," J. Kanicki and P. Wagner, October 19-24, 1986, San Diego, CA.
22. **172nd Electrochemical Society Meeting**, "Stable Photoinduced Paramagnetic Defects in Hydrogenated Amorphous Silicon Nitride," D. T. Krick, P. M. Lenahan, and J. Kanicki, October 18-23, 1987, Honolulu, HA.
23. **Tenth International Conference on Chemical Vapor Deposition**, "Comparative Study of Silicon Dioxide Films Deposited by Various Techniques," J. Kanicki, D. B. Buchanan, and B. Robinson, October 18-23, 1987, Honolulu, HA.
24. **First Workshop on Process-Related Electrically Active Defects in Semiconductor Systems**, "Stable Photo-Induced Paramagnetic Defects in Hydrogenated Amorphous Silicon Nitride," D.T. Krick, P. M. Lenahan, and J. Kanicki, September 1-2, 1987, Microelectronic Center of North Carolina Research Triangle Park, NC.
25. **1987 IEEE Semiconductor Interface Specialists Conference**, "Stable Photoinduced Paramagnetic Defects in Silicon Nitride," D.T. Krick, P.M. Lenahan and J. Kanicki, December 3-5, 1987, Ft. Lauderdale, FL
26. **SPIE Meeting on Spectroscopic Characterization Techniques for Semiconductor Technology III**, "Electron Spin Resonance Spectroscopy of Defects in Low Temperature Dielectric Films," D. Jousse, J. Kanicki, J. Batey, J. Stathis and Y. Cros, March 13-18, 1988, Newport Beach, CA.
27. **1988 March Meeting of the American Physical Society**, "Induced Instabilities in Silicon Nitride," D.T. Krick, P.M. Lenahan and J. Kanicki, March 21-25, 1988, New Orleans, LA.
28. **1988 Materials Research Society Spring Meeting**, "Role of Hydrogen in Silicon Nitride Films Prepared by Various Deposition Techniques," J. Kanicki, April 5-8, 1988, Reno, NV.
29. **1988 Materials Research Society Spring Meeting**, "Temperature Dependent Characteristics of Hydrogenated Amorphous Silicon Thin Film Transistor," N. Lustig, J. Kanicki, R. Wisnieff and J. Griffith, April 5-8, 1988, Reno, NV.

30. **1988 IEEE Int. Symp. on Electrical Insulation**, "Intrinsic Stress in Silicon Nitride and Silicon Dioxide Films Prepared by Various Deposition Techniques," J. Kanicki, P. Wagner, J. Karasinski and J. Angielello, June 5-8, 1988, Boston, MA.
31. **Rocky Mountain Conference**, "Nature of the Dominant Deep Trap in Amorphous Silicon Nitride," D.T. Krick, P.M. Lenahan and J. Kanicki, August 3, 1988, Denver, CO.
32. **1988 Electrochemical Society Fall Meeting**, "Nature of the Dominant Deep Trap in Amorphous Silicon Nitride," D.T. Krick, P.M. Lenahan and J. Kanicki, October 9-14, 1988, Chicago, IL.
33. **1988 Electrochemical Society Fall Meeting**, "High Quality Nitrogen-Rich PECVD  $a\text{-SiN}_x\text{:H}$  Films For Application in Thin Film Transistors," W.S. Lau, S.J. Fonash and J. Kanicki, October 9-14, 1988, Chicago, IL.
34. **1988 Electrochemical Society Fall Meeting**, "Mobile Ion Drift in High Quality PECVD  $a\text{-SiO}_x\text{:H}$  Films," G. Liu, W.S. Lau, S.J. Fonash and J. Kanicki, October 9-14, 1988, Chicago, IL.
35. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, "Nature of the Dominant Deep Trap in Amorphous Silicon Nitride," W.S. Lau, G. Liu, S.J. Fonash and J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.
36. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, "An Investigation of Mobile Ion-Like Instability in High Quality Nitrogen-Rich  $a\text{-SiN}_x\text{:H}$  Films and High Quality  $a\text{-SiO}_x\text{:H}$  Films Deposited by PFCVD," W.S. Lau, G. Liu, S.J. Fonash and J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.
37. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, "A TEM Study of Low Temperature Crystallized Amorphous Silicon Films," G. Liu, W.S. Lau, R. Kakkad, S.J. Fonash and J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.
38. **International Topical Conference on Hydrogenated Amorphous Silicon Devices and Technology**, "Direct Observation of Hydrogenated Amorphous Silicon / Silicon Nitride Interface States Distributed Within the Hydrogenated Amorphous Silicon Bandgap." A.V. Gelatos and J. Kanicki, November 21-23, 1988, Yorktown Heights, NY.

39. **1988 Materials Research Society Fall Meeting**, "Nature of the Dominant Deep Trap in Amorphous Silicon Nitride," D. T. Krick, P. M. Lenahan and J. Kanicki, November 28- December 3, 1988, Boston, MA.
40. **1989 American Physical Society Spring Meeting**, "Origin of Light Induced Effects in Silicon Nitride," J. Kanicki, D. Jousse and J.H. Stathis, March 20-24, 1989, St. Louis, MO.
41. **1989 American Physical Society Spring Meeting**, "Observation of Multiple Defect Configurations in Silicon Nitride," D. Jousse, J. Kanicki and J. H. Stathis, March 20-24, 1989, St. Louis, MO.
42. **Int. Conf. on Insulating Films on Semiconductors**, "Electron Spin Resonance Study of Metal-Nitride-Silicon Structures: Observation of Si Dangling Bonds with Different Configurations and Trapping Properties in Silicon Nitride," D. Jousse, J. Kanicki and J. H. Stathis, March 29-31, 1989, Munich, Germany.
43. **Int. Conf. on Insulating Films on Semiconductors**, "The Nature of the Dominant Deep Trap in Amorphous Silicon Nitride Films: Evidence for a Negative Correlation Energy," D.T. Krick, P.M. Lenahan and J. Kanicki, March 29-31, 1989, Munich, Germany.
44. **1989 Materials Research Society Spring Meeting**, "Properties of High Conductivity Phosphorous Doped Hydrogenated Microcrystalline Silicon and Application in Thin Film Transistor Technology," J. Kanicki, E. Hansan, J. Griffith, T. Takamori and J.C. Tsang, April 24-29, 1989, San Diego, CA.
45. **1989 Materials Research Society Spring Meeting**, "Properties and Application of Undoped Hydrogenated Microcrystalline Silicon Thin Films," J. Kanicki, E. Hasan, D.F. Kotecki, T. Takamori and J.H. Griffith, April 24-29, 1989, San Diego, CA.
46. **1989 Materials Research Society Spring Meeting**, "Investigation of the Interface Between Silicon Nitride and a-Si:H by Deep Level Transient Spectroscopy and Voltage Pulse Transient Photocapacitance," A.V. Gelatos and J. Kanicki, April 24-29, 1989, San Diego, CA.
47. **1989 Electrochemical Society Spring Meeting**, "Comparison of Thermally Grown and Plasma-Enhanced Chemical Vapor Deposited Silicon Dioxide Gate Dielectrics for Polycrystalline Silicon TFT's," M.K. Hatalis, S. Vincellette, J. Kanicki and P. Wagner, May, 1989, Los Angeles, CA.
48. **1989 Electronic Materials Conf.**, "The Nature of the Dominant Deep Trap in Amorphous Silicon Nitride Films: Evidence for a Negative Correlation Energy," D.T. Krick, P.M. Lenahan and J. Kanicki, June 21-23, 1989, Cambridge, MA.

49. **1989 Electronic Materials Conf**, "Comparative Study of the Silicon Nitride Amorphous Silicon and Silicon Nitride Crystalline Silicon Interfaces," A.V. Gelatos and J. Kanicki, June 21-23, 1989, Cambridge, MA.
50. **13th Int. Conf. on Amorphous and Liquid Semiconductors**, "Light Induced Effects in Hydrogenated Amorphous Nitrogen-Rich Silicon Nitride Films," J. Kanicki, D. Jousse, A. Gelatos and M.S. Crowder, August 21-25 1989, Asheville, NC.
51. **13th Int. Conf. on Amorphous and Liquid Semiconductors**, "Investigation of the Silicon Nitride Amorphous Silicon Interface by Capacitance Measurements," A.V. Gelatos and J. Kanicki, August 21-25, 1989, Asheville, NC.
52. **9th Int. Symp. on Plasma Chemistry**, "Properties of Device Quality Nitrogen-Rich Silicon Nitride Thin Films," J. Kanicki and D. Jousse, September 4-8, 1989, Pugnochiuso, Italy.
53. **1989 Materials Research Society Fall Meeting**, "Correlations Between Structural, Electrical and Optical Properties of in-Situ Phosphorous Doped Hydrogenated Microcrystalline Silicon-Effects of Rapid Thermal Annealing on Material Properties," D.E. Kotecki, S.J. Jeng, C J. Kanicki, C. Park, W. Rausch, K. Seshan and J. Tien, November 27-30, 1989, Boston, MA.
54. **1990 American Physical Society March Meeting**, "Photodarkening and Bleachingin Silicon Nitride," C.H. Seager and J. Kanicki, 12-16 March, 1990, Anaheim, CA.
55. **1990 American Physical Society March Meeting**, "Photo-bleaching of the LESR in Silicon Nitride," E.D. Tober, M.S. Crowder and J. Kanicki, 12-16 March, 1990, Anaheim, CA.
56. **1990 American Physical Society March Meeting**, "Evidence for a Negative Electron-Electron Correlation Energy in the Dominant Deep Trapping Center in Silicon Nitride Films," S.E. Curry, P.M. Lenahan, D.T. Krick and J. Kanicki, 12-16 March, 1990, Anaheim CA.
57. **1990 Materials Research Society Spring Meeting**, "Electron Spin Resonance in Nitrogen-Rich Gate-Quality Amorphous Silicon Nitride: Photoproduction, Photodepletion and Thermal Annealing," E.D. Tober, M.S. Crowder and J. Kanicki, April 16-21, 1990, San Francisco, CA.
58. **1990 Materials Research Society Spring Meeting**, "The Creation of Positive Charges in Gate-Quality Nitrogen-Rich Amorphous Silicon Nitride by Subbandgap UV-illumination," J. Kanicki and M. Sankaran, April 16-21, 1990, San Francisco, CA.

59. **1990 Materials Research Society Spring Meeting**, "Effect of Gate Dielectric on Performance of Polysilicon Thin Film Transistors," M.K. Hatalis, J. Kung, J. Kanicki and A.A. Bright, April 16-21, 1990, San Francisco, CA.
60. **20th Int. Conf. on the Physics of Semiconductors**, "Metastable Changes in Silicon Nitride Amorphous Silicon Structures Induced by Bias-Temperature Stress," J. Kanicki and A. Gelatos, August 6-10, 1990 Thessaloniki, Greece.
61. **20th Int. Conf on the Physics of Semiconductors**, "The Generation and Photobleaching of Light Induced Positive Charge in Amorphous Silicon Nitride by Subbandgap UV-illumination," J. Kanicki and M. Sankaran, August 6-10, 1990, Thessaloniki, Greece.
62. **1990 IEEE Semiconductor Interface Specialists Conference**, "Magnetic Resonance Investigation of Silicon and Nitrogen Dangling Bonds in Silicon Nitride," W.L. Warren, P.M. Lenahan and J. Kanicki, December 6-8, 1990, San Diego, CA.
63. **1991 American Physical Society March Meeting**, "Paramagnetic Nitrogen Defects in Silicon Nitride," W.L. Warren, P.M. Lenahan, F.C. Rong, E.H. Poindexter and J. Kanicki, March 18-22, 1991, Cincinnati, OH.
64. **1991 American Physical Society March Meeting**, "Kinetics of Photoinduced Trapping and Detrapping of Carriers in Amorphous Silicon Nitride Films," J. Kanicki, M. Sankaran, E.D. Tober, and M.S. Crowder, March 18-22, 1991, Cincinnati, OH.
65. **1991 Materials Research Society Spring Meeting**, "Influence of the Gate Bias and Temperature on Positive Charge Generation in TFT Gate Quality Amorphous Silicon Nitride Films," J. Kanicki and M. Sankaran, April 29-May 3, 1991, Anaheim, CA.
66. **179th Electrochemical Society Meeting**, "Hydrogenation of Polycrystalline Silicon Thin Film Transistors," M K. Hatalis, J.H. Kung and J. Kanicki, May 5-10, 1991, Washington, DC.
67. **1991 Materials Research Society Spring Meeting**, "Bias Stress Induced Instabilities in Amorphous Silicon Nitride/Polycrystalline Silicon and Amorphous Silicon Nitride / Amorphous Silicon Structures," J. Kanicki, C. Godet and A.V. Gelatos, April 29-May 3, 1991, Anaheim, CA.
68. **1991 Materials Research Society Spring Meeting**, "Thermal Annealing of Light-Induced K-Centers in Hydrogenated Amorphous Silicon Nitride," E.D. Tober, E. Sigari, J. Kanicki and M.S. Crowder, April 29-May 3, 1991, Anaheim, CA.

69. **Int. Worshop on Science and Technology of Thin Films for 21st Century**, "Investigations of Polysilicon Film Gate Dielectric Interface and Polysilicon Grain Size of Polycrystalline Silicon Thin Film Transistors," J. Kung, F. Lin M. Hatalis and J. Kanicki, July 28-August 2, 1991, Northwest University, Evanston, IL.
70. **14th Int. Conf. on Amorphous Semiconductors - Science and Technology**, "Silicon Dangling Bond Centers in Amorphous Silicon Nitride," P.M. Lenahan, D.T. Krick, W.L. Warren and J. Kanicki, August 19-23, 1991, Garmisch-Partenkirchen, Germany.
71. **14th Int. Conf. on Amorphous Semiconductors - Science and Technology**, "Microscopic Origin of the Light-Induced Defects in Hydrogenated Nitrogen-Rich Amorphous Silicon Nitride Films," J. Kanicki, W.L. Warren, C.H. Seager, M.S. Crowder and P.M. Lenahan, August 19-23, 1991, Garmisch-Partenkirchen, Germany.
72. **14th Int. Conf. on Amorphous Semiconductors - Science and Technology**, "Determination of Electron and Hole Mobilities in *a-Si:H* from Photo-electric Effects in Waveguide Structure," M. Zelikson, K. Weiser, J. Salzman and J. Kanicki, August 19-23, 1991, Garmisch-Partenkirchen, Germany.
73. **14th Int. Conf. on Amorphous Semiconductors - Science and Technology**, "Transient Photocapacitance and Capacitance Studies of Interface and Bulk States in Metal *a-SiN<sub>1.6</sub>:H / a-Si:Hc-Si* Devices," G. Godet, J. Kanicki and A. Gelatos, August 19-23, 1991, Garmisch-Partenkirchen, Germany.
74. **1991 Materials Research Society Fall Meeting**, "Optically Induced Paramagnetism in Amorphous Silicon Nitride," W.L. Warren, J. Kanicki, F.C. Rong, W.R. Buchwald, and M. Harmatz, December 2-6, 1991, Boston, MA.
75. **1991 Materials Research Society Fall Meeting**, "Structure, Characteristics, and the Application of Phosphorous Doped Hydrogenated Microcrystalline Silicon," S.J. Jeng, D.E. Kotecki, J. Kanicki, and C.C. Parks, December 2-6, 1991, Boston, MA.
76. **22nd IEEE Semiconductor Interface Specialists Conf.**, "Charge Trapping Centers in Silicon Nitride Thin Films," W.L. Warren, J. Kanicki, J. Robertson, E.H. Poindexter, C.H. Seager, and R.C. McWhorter, December 11-14, 1991, Lake Buena Vista, IL.
77. **Int. Semicon Device Research Symposium**, "Photocapacitance and Conductance Studies of Silicon Nitride/Crystalline Silicon Interface States Produced by Bias-Stressing," C. Godet and J. Kanicki, December 4-6, 1991, Charlottesville, VA.

78. **1992 American Physical Society March Meeting**, "Influence of Built-in Fields on the Electro-Optic Effect in an Amorphous Silicon Waveguide," M. Zelikson, K. Weiser, J. Sultzman and J. Kanicki, 16-20 March, 1992, Indianapolis, IN.
79. **1992 Materials Research Society Spring Meeting**, "Investigation of Hydrogen and Nitrogen Stability in PEVCD  $a\text{-SiN}_x\text{:H}$ ," D. Chen, J.M. Viner, P.C. Taylor and J. Kanicki, 27 April-1 May, 1992, San Francisco, CA.
80. **1992 Materials Research Society Spring Meeting**, "Investigation of Hydrogen and Nitrogen Stability in PEVCD  $a\text{-SiN}_x\text{:H}$ ," M. Fitzner, J.R. Abelson and J. Kanicki, April 27-May 1, 1992, San Francisco, CA.
81. **CLEO'92**, "Electrooptic Effect in an Amorphous Silicon Core Waveguide Structure," M. Zelikson, J. Sultzman, K. Weiser and J. Kanicki, May 10-15, 1992, Anaheim, CA.
82. **181st Electrochemical Society Meeting**, "Optically Induced Nitrogen Dangling Bonds in Amorphous Silicon Nitride Thin Films," W.L. Warren, J. Kanicki, R.C. McWhorter and E.H. Pointdexter, May 17-22, 1992, St. Louis, Missouri.
83. **7th Trieste Semicon. Symp. On Wide-Band Gap Semiconductors**, "Photocreation and Photobleaching of  $a\text{-SiN}_{1.6}\text{:H} / c\text{-Si}$  Interface States Studied by Photocapacitance Transient Spectroscopy," D. Godet and J. Kanicki, June 8-12, 1992, Trieste, Italy.
84. **50th Annual Device Research Conf.**, "Hydrogenation Effects on Polysilicon Thin Film Transistor Structures," M.K. Hatalis, J.H. Kung and J. Kanicki, June 22-24, 1992, Boston, MA.
85. **21st Int. Conf. on the Physics of Semiconductors**, "Electro-optic Effects in an Amorphous Silicon Waveguide," M. Zelikson, J. Sultzman, K. Weiser and J. Kanicki, August 10-14, 1992, Beijing, China.
86. **Int. Conf. on Solid State Devices and Materials**, "A Simple Polysilicon Thin Film Transistor Structure for Achieving High On/Off Current Ratio Independent of Gate Bias," J. Kanicki and M. Hatalis, August 26-28, 1992, Tsukuba, Japan.
87. **Int. Conf. on Solid State Devices and Materials**, "Bias-Stress Induced Stretched-Exponential Time Dependence of Charge Injection and Trapping in Amorphous Silicon Thin Film Transistors," F.R. Libsch and J. Kanicki, August 26-28, 1992, Tsukuba, Japan.
88. **Int. Conf. on Solid State Devices and Materials**, "Nitrogen Dangling Bonds in Hydrogenated Amorphous Silicon Nitride Thin Films," J. Kanicki, W.L. Warren and E.H. Poindexter, August 26-28, 1992, Tsukuba, Japan.

89. **12th Int. Display Research Conf.**, "A New Threshold Voltage Shift Estimation Method for Bias Temperature Stress of Amorphous Silicon Thin Film Transistors," F.R. Libsch and J. Kanicki, October 12-14, 1992, Hiroshima, Japan.
90. **39th Nat. American Vacuum Society Symp. & Topical Confs.**, "Investigation of Hydrogen and Nitrogen Thermal Stability in PECVD  $a\text{-SiN}_x\text{:H}$ ," M. Fitzner, J.R. Abelson and J. Kanicki, November 9-13, 1992, Chicago, IL.
91. **1992 Materials Research Society Fall Meeting**, "Experimental Evidence for Correlation Energy of Defect Centers in N-rich Hydrogenated Amorphous Silicon Nitride," J. Kanicki, W.L. Warren and C.H. Seager, November 30-December 4, 1992, Boston, MA.
92. **1992 Materials Research Society Fall Meeting**, "The Effect of UV Light on the Infra-red Absorption Properties of Chemically Vapor Deposited  $a\text{-SiN}_x\text{:H}$  Films," C.H. Seager and J. Kanicki, November 30 - December 4, 1992, Boston, MA.
93. **1992 Materials Research Society Fall Meeting**, "Paramagnetic Nitrogen Defects in Silicon Nitride," W.L. Warren, J. Kanicki, J. Robertson and E.H. Poindexter, November 30-December 4, 1992, Boston, MA.
94. **1992 Materials Research Society Fall Meeting**, "Performance of Polycrystalline Silicon Thin Film Transistors with Double Layer Gate Dielectric." J.H. Kung, M. Hatalis and J. Kanicki, November 30-December 4, 1992, Boston, MA.
95. **23rd IEEE Semicon. Interface Specialists Conf.**, "Nitrogen Defect Centers in Silicon Nitride Thin Films," W.L. Warren, J. Kanicki, J. Robertson, R.C. McWhorter and E.H. Poindexter, December 9-12, 1992, San Diego, CA.
96. **1993 Society for Information Display Meeting**, "TFT Lifetime in LCD Operation," F.R. Libsch and J. Kanicki, May 16-21, 1993, Seattle, WA.
97. **1993 Society for Information Display Meeting**, "Low Temperature Poly-Si TFTs on Corning Code 1734 and 1735 Glass Substrates," M.K. Hatalis, D.N. Kouvatsos, J.-H. Kung, A.T. Voutsas, F.R. Fehlner and J. Kanicki, May 16-21, 1993, Seattle WA.
98. **Active-Matrix Liquid-Crystal Displays Symposium**, "DC and Pulsed Reliability of  $a\text{-Si:H}$  TFTs in XGA LCD Operation," E.F. Libsch and J. Kanicki, October 21-22, 1993, Bethlehem, PA.
99. **Active-Matrix Liquid-Crystal Displays Symposium**, "Effect of Grain Size and Device Structure on Poly-Si TFT Performance," M.K. Hatalis, D.N. Kouvatsos, J.-H. Kung, S.H. Lin and J. Kanicki, October 21-22, 1993, Bethlehem, PA.

100. **1994 Materials Research Society Spring Meeting**, "Photobleaching of PL and Temperature Dependence of EPR in Nitrogen-Rich Amorphous Silicon Nitride Films," D. Chen, J.M. Viner, P.C. Taylor, and J. Kanicki, April 4-8, 1999, San Francisco, CA.
101. **1994 European Materials Research Society Spring Meeting**, "Nature of the Si and N Dangling Bonds in Silicon Nitride," J. Roberson, W.L. Warren and J. Kanicki, May 24-27, 1994, Strasbourg, France.
102. **1994 European Materials Society Spring Meeting**, "Measurements of Interface States in Top Gate  $a\text{-SiN}_x\text{:H}$  /  $a\text{-Si:H}$  Structures," J. Kanicki and S. Backert, May 24-27, 1994, Strasbourg, France.
103. **1995 Int. Conf. on Solid State Devices and Materials**, "Interface States in Top Gate Metal-Silicon Nitride-Silicon Structures," J. Kanicki, S. Backert and N. Picard, August 21-27, 1995, Osaka, Japan.
104. **1995 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, "UV-Light Induced Changes in Polyimide LC Alignment Films," J.Lu, S. Deshpande, J. Kanicki, A. Lien, R.A. John, and W.L. Warren, August 24-25, 1995, Osaka, Japan.
105. **1995 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, "Simulation of the High Performance  $a\text{-Si:H}$  TFT for High Definition LCDs," C.-Y. Chen and J. Kanicki, August 24-25, 1995, Osaka, Japan.
106. **2<sup>nd</sup> Int. Workshop on Active-Matrix Liquid-Crystal Displays**, "Simulation of Influence of Density of States in  $a\text{-Si:H}$  on Electrical Performance of  $a\text{-Si:H}$  Thin Film Transistors," C.-Y. Chen and J. Kanicki, September 25-26, 1995, Bethlehem, PA.
107. **2<sup>nd</sup> Int. Workshop on Active-Matrix Liquid-Crystal Displays**, "Electrical Performance of Top-Gate Amorphous Silicon Thin Film Transistors," C.-S. Chiang, J. Kanicki and F.R. Libsch, September 25-26, 1995, Bethlehem, PA.
108. **2<sup>nd</sup> Int. Workshop on Active-Matrix Liquid-Crystal Displays**, "An Alternative Transparent Conducting Oxide to ITO for the  $a\text{-Si:H}$  TFT-LCD Applications," J.-H. Lan and J. Kanicki, September 25-26, 1995, Bethlehem, PA.
109. **2<sup>nd</sup> Int. Workshop on Active-Matrix Liquid-Crystal Displays**, "Investigation of Hydrogen Evolution and Dangling Bonds Creation Mechanism in Amorphous Silicon Nitride Thin Films," T. Li, J. Kanicki, M. Fitzner, and W.L. Warren, September 25-26, 1995, Bethlehem, PA.
110. **1996 Materials Research Society Spring Meeting**, "Selective Deposition of Polysilicon at Low Temperature by Hot-Wire CVD," S. Yu, E. Gulari and J. Kanicki, April 8-12, 1996, San Francisco, CA.

111. **1996 Materials Research Society Spring Meeting**, "Atomic Hydrogen Effects on the Optical and Electrical Properties of Transparent Conducting Oxides for Flat Panel Displays," J.-H. Lan and J. Kanicki, April 8-12, 1996, San Francisco, CA.
112. **1996 Materials Research Society Spring Meeting**, "Influence of the Density of States and Temperature-Dependent Contact Resistance on the Field-Effect Activation Energy in *a-Si:H TFT*," C.-Y. Chen and J. Kanicki, April 8-12, 1996, San Francisco, CA,
113. **1996 Materials Research Society Spring Meeting**, "Poly (Bithiazoles): A New Class of Polymers for Light-Emitting Diodes," D. Curtis, J.K. Politis, J. Nanos, and J. Kanicki, April 8-12, 1996, San Francisco, CA.
114. **1996 Materials Research Society Spring Meeting**, "High-Rate Deposited Amorphous Materials for the Hydrogenated Amorphous Silicon Thin Film Transistor Structures," T. Li, C.-Y. Chen, J. Kanicki and C. Malone, April 8-12, 1996, San Francisco, CA.
115. **IEEE 54<sup>th</sup> Device Research Conf.**, "High Field-Effect Mobility *a-Si:H TFT* Based on High Deposition Rate Materials," C.-Y. Chen and J. Kanicki, June 24-26, 1996, Santa Barbara, CA.
116. **16<sup>th</sup> Int. Display Research Conf.**, "AMLCD Lifetime Evaluation Based on A.C. Electrical Instability of Amorphous Silicon Thin Film Transistors," C.-S. Chiang, J. Kanicki, S. Nishida and K. Takechi, October 1-3, 1996, Birmingham, U.K.
117. **3<sup>rd</sup> Int. Display Workshops**, "Electrical Performance and Instability of High Field Effect Mobility *a-Si:H TFTs* Made from High Deposition Rate PECVD Materials," C.-Y. Chen, C.-S. Chiang, C. Malone and J. Kanicki, November 27-29, 1996, Kobe, Japan.
118. **3<sup>rd</sup> Int. Display Workshops**, "*a-Si:H TFT-LCD Lifetime Evaluation with Gate-Line Delay Consideration*," C.-S. Chiang, J. Kanicki, S. Nishida and K. Takechi, , November 27-29, 1996, Kobe, Japan.
119. **1996 Materials Research Society Fall Meeting**, "Characterization of Instability in High-Rate Deposited Hydrogenated Amorphous Silicon Nitride Thin Films," T. Li, C.-Y. Chen, J. Kanicki and C. Malone, December 2-6, 1996, Boston, MA.
120. **1997 SPIE Meeting, Symposium on Active Matrix Liquid Crystal Displays Technology and Applications**, "Gated-Four-Probe TFT Structure: a New Technique to Measure the Intrinsic Performance of *a-Si:H TFT*," C.-Y. Chen and J. Kanicki, Symposium on "Active Matrix Liquid Crystal Displays Technology and Applications," February 10-11, 1997, San Jose, CA.

121. **1997 Materials Research Society Spring Meeting**, “*Aluminum Gate Metallization for AMLCDs*,” J.-H. Kim, J. Kanicki and W. den Boer, March 31-April 3, 1997, San Francisco, CA.
122. **1997 Materials Research Society Spring Meeting**, “*Electrical Characteristics of New LDD Poly-Si TFT with Mis-alignment Tolerant Structure for AMLCDs*,” B.-H. Min and J. Kanicki, March 31 – April 3, 1997, San Francisco, CA.
123. **1997 Society for Information Display Int. Symp.**, “*Electric Stability of Short-Channel Poly-Si TFTs Fabricated by SPC and ELA for AMLCDs*,” B.-H. Min, J.-H. Kim, J. Kanicki and G. Fortunato, May 13-15, 1997, Boston, MA.
124. **55<sup>th</sup> Device Research Conf.**, “*Gated-Four-Probe a-Si:H Thin-Film Transistor Structure*,” C.-Y. Chen, C.-S. Chiang and J. Kanicki, June 23-25, 1997, Boulder, CO.
125. **1997 Int. Workshop on “Active-Matrix Liquid-Crystal Displays”**, “*Analysis of the Pixel Unit Cell Incorporating Planarization Polymer for the High-Aperture-Ratio a-Si:H TFT-LCDs*,” J.-H. Lan and J. Kanicki, September 11-12, 1997, Tokyo, Japan.
126. **1997 Int. Workshop on “Active-Matrix Liquid-Crystal Displays”**, “*Analysis of the Amorphous Silicon Thin Film Transistors Behavior Under Illumination*,” S. Martin, J. Kanicki, N. Szydlo and A. Rolland, September 11-12, 1997, Tokyo, Japan.
127. **1997 Int. Display Res. Conf.**, “*Aluminum Gate Metallization for High-Performance a-Si:H TFTs Fabricated from High-Deposition Rate PECVD Materials*,” C.-Y. Chen, B.-H. Min and J. Kanicki, September 15-19, 1997, Toronto, Canada.
128. **1997 Int. Display Res. Conf.**, “*Electrical Characteristics of Top-Gate a-Si:H TFTs for AMLCDs*,” C.-S. Chiang and J. Kanicki, September 15-19, 1997, Toronto, Canada.
129. **1997 Int. Display Res. Conf.**, “*Analysis of Amorphous Silicon Thin Film Transistors Behavior in the Dark and Under Illumination: Sensitivity to Geomeytric Parameters*,” S. Martin, J. Kanicki, N. Szydlo and Rolland, September 15-19, 1997, Toronto, Canada.
130. **1997 Int. Display Res. Conf.**, “*Planarization of Amorphous Silicon Thin Film Transistor for the High-Aperture-Ratio Active-Matrix Liquid-Crystal Displays*,” J.-H. Lan and J. Kanicki, September 15-19, 1997, Toronto, Canada.

131. **83<sup>rd</sup> Radiological Society of North America Meeting**, “*High Fidelity Electronic Display of Digital Radiographs*,” M.J. Flynn, J. Kanicki, A. Badano and W.R. Eyer, November 1997, Chicago, IL.
132. **1998 SPIE Int. Symp. on Medical Imaging**, “*The Effect of Secondary Radiations on the Performance of Digital Radiographic Detectors*,” M.J. Flynn, S. Wilderman and J. Kanicki, February 21-27, 1998, San Diego, CA.
133. **1998 Materials Research Society Spring Meeting**, “*Effects of Ultraviolet-Light on Polyimide Films for Liquid Crystal Alignment*,” S. Gong, J. Kanicki, L. Ma and J.Z.Z. Zhong, April 13-17, 1998, San Francisco, CA.
134. **1998 Materials Research Society Spring Meeting**, “*Longitudinal Vibrational Absorption Modes of Hydrogenated Amorphous Silicon Nitride Thin Films*,” T. Li and J. Kanicki, April 13-17, 1998, San Francisco, CA.
135. **1998 Society for Information Display Int. Symp.**, “*Full-Color Light-emitting Devices Based on  $\pi$ - and  $\sigma$ -Conjugated Polymer Materials*,” R. Hattori, Y. He, J. Kanicki, T. Sugano and T. Fujiki, May 17-22, 1998, Anaheim, CA.
136. **1998 Society for Information Display Int. Symp.**, “*High-Performance Top-Gate a-Si:H TFTs for AMLCDs*,” C.-S. Chiang, S. Martin, J.-Y. Nahm, J. Kanicki, Y. Ugai, T. Yukawa and S. Takeuchi, May 17-22, 1998, Anaheim, CA.
137. **1998 Society for Information Display Int. Symp.**, “*UV-Light Modified Polyimide Films for Liquid-Crystal Alignment*,” S. Gong, J. Kanicki, L. Ma and J.Z.Z. Zhong, May 17-22, 1998, Anaheim, CA.
138. **56<sup>th</sup> Device Research Conf.**, “*Planarized Copper Gate Hydrogenated Amorphous Silicon Thin-Film Transistors for AM-LCDs*,” J.-H. Lan and J. Kanicki, June 22-24, 1998, Charlottesville, VA.
139. **1998 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*A Novel Wide Viewing Angle Twisted-Nematic LCD Structure*.” S. Gong, G. Xu and J. Kanicki, July 9-10, 1998, Tokyo, Japan.
140. **1998 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*A Novel Wide Viewing Angle Twisted-Nematic LCD Structure*.” S. Gong, G. Xu and J. Kanicki, July 9-10, 1998, Tokyo, Japan.
141. **1998 Int. Workshop on Active-Matrix Liquid-Crystal Displays (AM-LCD'98)**, “*A Novel Wide Viewing Angle Twisted-Nematic LCD Structure*,” S. Gong, G. Xu and J. Kanicki, July 9-10, 1998, Tokyo, Japan.
142. **1998 Int. Workshop on Active-Matrix Liquid-Crystal Displays**, “*Amorphous Silicon Thickness Dependence of Top-Gate Thin-Film Transistors*,” S. Martin, C.-

- S. Chiang, J. Kanicki, Y. Ugai, T. Yukawa and S. Takeuchi, July 9-10, 1998, Tokyo, Japan.
143. **1988 Int. Workshop on Active-Matrix Liquid-Crystal Displays (AM-LCD'98)**, “*Fully Planarized a-S:H TFTs for AM-LCDs*,” J.-H. Lan, J. Kanicki and M. Radler, July 9-10, 1998, Tokyo, Japan.
144. **1998 Int. Conf. On Solid State Devices and Materials**, “*Two-Dimensional Numerical Simulation of Solid-Phase-Crystallized Polysilicon TFT Characteristics*,” T.-K. Chou and J. Kanicki, September 7-10, 1998, Hiroshima, Japan.
145. **Flat Panel and Vehicle Display '98**, “*Reflective AMLCs*,” J. Kanicki, S. Martin, J.-Y. Nahm and Y. Ugai, September 9-10, 1998, Ypsilanti, MI.
146. **18<sup>th</sup> Int. Display Res. Conf. (Asia Display '98)**, “*Amorphous Silicon Thin-Film Transistor Active-Matrix Reflective Cholesteric Liquid Crystal Display*,” J.Y. Nahm, T. Goda, B.H. Min, T.K. Chou, J. Kanicki, X.Y. Huang, N. Miller, V. Sergan, P. Bos and J.W. Doane, September 28-October 1, 1998, Seoul, Korea.
147. **18<sup>th</sup> Int. Display Res. Conf. (Asia Display '98)**, “*OLED Based Display for Automotive Applications*,” Y. He, S. Gong, R. Hattori and J. Kanicki, September 28–October 1, 1998, Seoul, Korea.
148. **1998 Electrochemical Society Meeting**, “*On the Evolution of Defect-Related Structure in the X-ray Absorption Spectra of PECVD SiN<sub>x</sub> Films*,” E.C. Paloura and J. Kanicki, November 1-6, 1998, Boston, MA.
149. **84<sup>th</sup> Radiological Society of North America Meeting**, “*Contrast Reduction from Ambient Light for Film, CRT, and AM-LCD Display Devices*,” M. Flynn, A. Badano and J. Kanicki, November 29-December 4, 1998, Chicago. IL.
150. **1999 SPIE Conf. on Electroactive Polymer Actuators and Devices**, “*Organic Polymer Light-Emitting Devices on the Plastic Substrates*,” Y. He, S. Gong and J. Kanicki, March 1-2, 1999, Newport Beach, CA.
151. **1999 Materials Research Society Spring Meeting**, “*A High-Voltage Hydrogenated Amorphous Silicon Thin-Film Transistor for Reflective Active-Matrix Cholesteric LCD*,” J.Y. Nahm, J.H. Lan, T.K. Chou, B.H. Min, T. Goda and J. Kanicki, April 5-9, 1999, San Francisco, CA.
152. **1999 Society for information Display Int. Symposium**, “*Small-Spot Contrast Measurements in High-Performance Displays*,” A. Badano, M.J. Flynn and J. Kanicki, May 18-20, 1999, San Jose, CA.

153. **41<sup>st</sup> Electronic Materials Conf.**, “*Highly Efficient Organic Polymer Light-Emitting Devices on Plastic Substrates*,” Y. He and J. Kanicki, June 30-July 2, 1999, Santa Barbara, CA.
154. **1999 Int. Workshop on “Active-Matrix Liquid-Crystal Displays,”** “*Electrical Instabilities of Top-Gate a-Si:H TFTs for AMLCDs*,” S. Martin, J. Kanicki and Y. Ugai, July 14-16, 1999, Tokyo, Japan.
155. **1999 Int. Workshop on “Active-Matrix Liquid-Crystal Displays,”** “*Buried Busline a-Si:H TFT Structures for AM-LCDs*,” J.-H. Lan, J.-Y. Nahm and J. Kanicki, July 14-16, 1999, Tokyo, Japan.
156. **The 19<sup>th</sup> Int. Display Res. Conf. (EuroDisplay ’99),** “*High-Efficiency Organic Polymer Light-Emitting Heterostructure Devices on Flexible Plastic Substrates*,” Y. He and J. Kanicki, September 6-9, 1999, Berlin, Germany.
157. **The 19<sup>th</sup> Int. Display Res. Conf. (EuroDisplay ’99),** “*Buried Busline Structure for Large-Area, High-Resolution, and High-Aperture-Ratio AM-LCDs*,” J.-H. Lan, J.-Y. Nahm and J. Kanicki, September 6-9, 1999, Berlin, Germany.
158. **The 19<sup>th</sup> Int. Display Res. Conf. (EuroDisplay ’99),** “*Top-Gate a-Si:H TFTs for AM-LCDs: a-Si:H Thickness Effect and Electrical Instabilities*,” S. Martin, J. Kanicki and Y. Ugai, September 6-9, 1999, Berlin, Germany.
159. **Society for information Display Conf. on “Vehicle Displays and Microsensors ’99,”** “*Planarization Technology of AMLCD*,” J.-H. Lan and J. Kanicki, September 22-23, 1999. Ypsilanti, MI.
160. **1999 OSA Meeting on “Organic Thin Films for Photonics Applications,”** “*Monte Carlo Modeling Method for Light Transport in Organic Thin Film Light-Emitting Devices*,” A. Badano and J. Kanicki, September 24-26, 1999, Santa Clara, CA.
161. **85<sup>th</sup> Radiological Society of North America Meeting,** “*Medical Imaging Displays Based on Active-Matrix Thin Film Organic Polymer Light Emitting Devices*,” A. Badano, J. Kanicki, Y. He and M.J. Flynn, November 28-December 3, 1999, Chicago. IL.
162. **1999 Int. Electron Devices Meeting,** “*Hydrogenated Amorphous Silicon Thin film Transistor Structure with the Buried Field Plate*,” J.-Y. Nahm, J-H. Lan and J. Kanicki, December 5-8, 1999, Washington, DC.
163. **2000 Device Research Conference,** “*Five-Terminal Amorphous Silicon Thin-Film Transistor Structure*,” S. Martin, Y. Feillens and J. Kanicki., June 19-21, 2000, Denver, CO.

164. **2000 SPIE's Annual Meeting**, “*Materials and Device Structures for High-Performance OLEDs*,” Y. Hong, Z. Hong, and J. Kanicki, July 30-August 2, 2000, San Diego, CA.
165. **2000 SPIE's Annual Meeting**, “*Polyfluorene Light Emitting Devices on Flexible Plastic Substrates*,” Y. He and J. Kanicki, July 31-August 2, 2000, San Diego, CA.
166. **Society for information Display, 20<sup>th</sup> Int. Display Research Conf.**, “*Organic Light Emitting Devices on Plastic Flexible Substrates: New Cathode and Light Emissive Materials*,” Y. Hong, Z. Hong, M.D. Curtis, and J. Kanicki, September 25-28, 2000, Palm Beach, FL.
167. **Society for information Display, 20<sup>th</sup> Int. Display Research Conf.**, “*Gate Planarized a-Si:H TFTs with the Silicon-Based Flowable Oxide*,” J. Kim and J. Kanicki, September 25-28, 2000, Palm Beach, FL.
168. **Society for Inf. Display, 20<sup>th</sup> International Display Research Conference**, “*Many Body Universal Approach to a-Si:H TFTs Electrical Instabilities*,” S. Martin, J.-Y. Nahm, J. Kim and J. Kanicki, September 25-28, 2000, Palm Beach, FL.
169. **Society for Inf. Display, 20<sup>th</sup> International Display Research Conference**, “*Five-Terminal Thin-Film Transistor Structure*,” S. Martin, Y. Feillens and J. Kanicki, September 25-28, 2000, Palm Beach, FL.
170. **Society for Inf. Display, 20<sup>th</sup> Int. Display Research Conf.**, “*Electrical Reliability of Two –and Four-a-Si:H TFT Pixel Electrode Circuits for Active-Matrix OLEDs*,” Y. He, R. Hattori and J. Kanicki, September 25-28, 2000, Palm Beach, FL.
171. **6<sup>th</sup> Int. Conf. on the Science and Technology of Display Phosphors**, “*Organic Polymer Light-Emitting Devices and Displays on Plastic Flexible Substrate*,” J. Kanicki, Y. He, Y. Hong, Z. He, Z. Hong, and A. Badano, November 6-8, 2000, San Diego, CA.
172. **2000 IEEE International Electron Device Meeting**, “*Fingerprint Imager Based on a-Si:H Active-Matrix Photo-Diode Arrays*,” J. Lan, A. Cole, J. VanZandt, A. Dickinson, F. Van de Ven, N. Bird, A. Badano and J. Kanicki, December 11-13, 2000, San Francisco, CA.
173. **IS&T / SPIE 13<sup>th</sup> Int. Symposium on Electronic Imaging 2001 – Science and Technology**, “*a-Si:H Pixel Electrode Circuits for AM-OLEDs*,” J. Kanicki, Y. He and R. Hattori, January 21-26, 2001, San Jose, CA.

174. **2001 IS&T / SPIE 13<sup>th</sup> Int. Symposium on Electronic Imaging – Science and Technology**, “*Characterization of Crosstalk in high-Resolution Active-Matrix Liquid Crystal Displays for Medical Imaging*,” A. Badano and J. Kanicki, Flat Panel Display Technology and Display Metrology II, January 22-23, 2001, San Jose, CA.
175. **Medical Imaging 2001, SPIE Annual Meeting**, “*Advanced Amorphous Silicon Thin Film Transistor Active-Matrix Organic Light-Emitting Displays Design for Medical Imaging*,” J. Kim and J. Kanicki, February 18-20, 2001, San Diego, CA.
176. **Medical Imaging 2001, SPIE Annual Meeting**, “*Color and Contrast Perception in Monochrome Medical Imaging Flat-Panel Displays*,” A. Badano and J. Kanicki, February 18-20, 2001, San Diego, CA.
177. **2001 Materials Research Society Spring Meeting**, “*Amorphous Silicon Thin Film Transistor Pixel Electrode Circuits for Active-matrix organic light-emitting displays*,” J. Kanicki and J. Kim, April 16-20, 2001, San Francisco, CA.
178. **2001 Materials Research Society Spring Meeting**, “*Amorphous Silicon Thin Film Transistor Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays*,” J. Kanicki, April 16-20, 2001, San Francisco, CA.
179. **2001 59<sup>th</sup> Device Research Conference**, “*Electrical Instabilities of Organic Polymer Thin-Film Transistors*,” S. Martin and J. Kanicki., June 25-27, 2001, Notre Dame, IN.
180. **2001 43<sup>rd</sup> Electronic Materials Conference**, “*Electrical Performances and Physics of Organic Polymer Thin Film Transistors*,” S. Martin and J. Kanicki, June 27-29, 2001, Notre Dame, IN.
181. **2001 Int. Workshop on “Active-Matrix Liquid Crystal Displays”**, “*Analog-Circuit Simulation of the Current-Programmed Active-Matrix Pixel Electrode Circuits Based on Poly-Si TFT for Organic Light-Emitting Displays*,” R. Hattori, Y. Kuroki and J. Kanicki, July 11-13, 2001, Tokyo, Japan.
182. **2001 46<sup>th</sup> SPIEs (The International Society for Optical Engineering) Annual Meeting**, “*High Performance Organic Polymer Light-Emitting Devices (OLEDs) with Two-Stacked Double Layers on Flexible Plastic Substrates*,” Y. Hong and J. Kanicki, July 29-August 1, 2001, San Diego, CA.
183. **2001 46<sup>th</sup> SPIE’s (The International Society for Optical Engineering) Annual Meeting**, “*Air-Stable Organic Polymer Red Light-Emitting Devices on Flexible Plastic Substrates*,” Y. Hong, Z. He, S. Lee, and J. Kanicki, July 30-August 1, 2001, San Diego, CA.

184. **3<sup>rd</sup> Int. Conf. on “Electroluminescence of Molecular Materials and Related Phenomena,”** “Optimization of Organic Polymer Red Light-Emitting Devices on Flexible Plastic Substrates,” Y. Hong, S. Lee, and J. Kanicki, September 5-8, 2001, Los Angeles, CA.
185. **3<sup>rd</sup> Int. Conf. on “Electroluminescence of Molecular Materials and Related Phenomena,”** “Monte Carlo Simulation of Spectral Photon Emission of the Organic Polymer Light-Emitting Devices,” S. Lee, A. Badano, Y. Hong, and J. Kanicki, September 5-8, 2001, Los Angeles, CA.
186. **3<sup>rd</sup> Int. Conf. on “Electroluminescence of Molecular Materials and Related Phenomena,”** “Active - Matrix Pixel Electrode Circuits for 500 dpi Organic Light-Emitting Displays,” J. Kim and J. Kanicki, September 5-8, 2001, Los Angeles, CA.
187. **Asia Display / IDW ‘01,** “Organic Polymer Light-Emitting Devices on Flexible Plastic Substrates for AM-OPLED,” Y. Hong, S. Lee, Z. He, and J. Kanicki, October 16-19, 2001, Nagoya, Japan.
188. **Medical Image Perception Conf. IX,** “Optimal Color for Supra-Threshold and Threshold Contrast Perception,” A. Badano, J. Kim and J. Kanicki, September 20-23, 2001, Warrenton, VA.
189. **Asia Display / IDW ‘01,** “Photosensitivity of a-Si:H TFTs,” J.-D. Gallezot, S. Martin and J. Kanicki, October 10-19, 2001, Nagoya, Japan.
190. **Asia Display / IDW ‘01,** “Two Photo-Mask Fully Self-Aligned Al Bottom-Gate a-Si:H TFTs,” J.H. Kim and J. Kanicki, October 10-19, 2001, Nagoya, Japan.
191. **RSNA’01,** “Angular Dependence of the Luminance and Contrast in Medical Imaging Monochrome Active-Matrix Liquid Crystal Displays,” A. Badano, M. Flynn, S. Martin and J. Kanicki, November 25-30, 2001, Chicago, IL.
192. **RSNA’01,** “Image Quality Characterization of Medical Imaging Monochrome Active-Matrix Liquid Crystal Displays,” A. Badano, S. Martin and J. Kanicki, November 25-30, 2001, Chicago, IL.
193. **Medical Imaging 2002: Visualization, Image-Guided Procedures, and Display,** “Amorphous Silicon Thin-Film Transistors-Based Active-Matrix Organic Light-Emitting Displays for Medical Imaging,” J.H. Kim and J. Kanicki, February 24-26, 2002, San Diego, CA.
194. **Medical Imaging 2002: Visualization, Image-Guided Procedures, and Display,** “Characterization of a High Quality Monochrome AM-LCD Monitor for Digital Radiology,” S. Martin, A. Badano and J. Kanicki, February 24-26, 2002, San Diego, CA.

195. **2002 IMAPS (International Microelectronics and Packaging Society)** Advanced Technology Workshop on Printing an Intelligent Future, “*Gate-Planarized Organic Polymer Thin-Film Transistors*,” S. Martin, J. Kanicki, M. Dibbs, D. Brennan and D. Welsh, March 8-10, 2002, Lake Tahoe, NE.
196. **2002 Society for Information Display Int. Symp.**, “*Novel Poly-Si TFT Pixel Electrode Circuits and Current Programmed Active-Matrix Driving Methods for AM-OLEDs*,” Y. Hong, R. Hattori, and J. Kanicki, May 21-23, 2002, Boston, MA.
197. **2002 Society for Information Display Int. Symp.**, “*Amorphous Silicon Thin-Film Transistors-Based Active-Matrix Organic Light-Emitting Display*,” J. Kim and J. Kanicki, May 21-23, 2002, Boston, MA.
198. **Electron, Ion and Photo Beam, and Nanotechnology 2002**, “*Nanoimprinted Organic Polymer Light-Emitting Devices for AM-OP-LEDs*,” X. Cheng, Y. Hong, J. Kanicki, and L.J. Guo, May 28-30, 2002, Anaheim, CA.
199. **2002 SPIE’s (The International Society for Optical Engineering) Annual Meeting**, “*Integrating Sphere CCD-Based Measurement Method of the OP-LED Optoelectronic Characteristics*,” Y. Hong and J. Kanicki, July 8-10, 2002, Seattle, WA.
200. **2002 SPIE’s (The International Society for Optical Engineering) Annual Meeting**, “*Mote Carlo Modeling of Organic Polymer Light-Emitting Devices on Flexible Plastic Substrates*,” S.J. Lee, A. Badano and J. Kanicki, July 8-10, 2002, Seattle, WA.
201. **2002 SPIE’s (The International Society for Optical Engineering) Annual Meeting**, “*Efficient and Saturated Blue Organic Ploymer Light Emitting Devices with an Oxidiazole Containing Poly(fluorine) Ploymer Emissive Layer*,” S.J. Lee, J.R. Gallegos, J. Klein, M.D. Curtis and J. Kanicki, July 8-10, 2002, Seattle, WA.
202. **2002 SPIE’s Annual Meeting**, “*Comparison Between Lens-Coupled and Integrating Sphere CCD-Based Measurement Methods of the OP-LED Optoelectronic Characteristics*,” Y. Hong and J. Kanicki, July 29-August 3, 2002, Seattle, WA.
203. **2002 SPIE’s Annual Meeting**, “*High-Resolution Transmission Electron Microscopy (HR-TEM) Study of the OP-LED Structures on Flexible Plastic Substrates*,” Y. Hong and J. Kanicki, July 29-August 3, 2002, Seattle, WA.
204. **2002 EL International Conf. on the Science and Technology of Emissive Displays and Lighting**, “*Three - Amorphous Silicon Thin-Film Transistors*

- Active-Matrix Organic Polymer Light-Emitting Displays,"* J. Kim and J. Kanicki, September 23-26, 2002, Ghent, Belgium.
205. **DoD Breast Cancer Research Program Meeting,** "Optimal Color for Supra-threshold and Threshold Contrast Perception," A. Badano, J.H. Kim and J. Kanicki, September 25-28, 2002, Orlando, FL.
206. **2002 EuroDisplay, The 22<sup>nd</sup> International Display Research Conf.,** "Three - Amorphous Silicon Thin-Film Transistors-Based Active-Matrix Organic Polymer Light-Emitting Displays," J. Kim and J. Kanicki, October 2-4, 2002, Nice, France.
207. **2002 EuroDisplay, The 22<sup>nd</sup> International Display Research Conf.,** "Organic Polymer Thin-Film Transistors for Active-Matrix Flat-Panel Displays?" S. Martin and J. Kanicki, October 2-4, 2002, Nice, France.
208. **2002 EuroDisplay, The 22<sup>nd</sup> International Display Research Conf.,** "High-Resolution Medical Imaging AM-LCD: Contrast Performance Evaluation," S. Martin, A. Badano and J. Kanicki, October 2-4, 2002, Nice, France.
209. **2002 EuroDisplay, The 22<sup>nd</sup> International Display Research Conf.,** "Printed Micron-Scale Organic Polymer Light-Emitting Devices for AM-OPLED," Y. Hong, X. Cheng, L. Jay Guo and J. Kanicki, October 2-4, 2002, Nice, France.
210. **2003 MRS Spring Meeting,** "Organic Polymer Devices Based on Super-Yellow Polymer," J. Kanicki, M. Pauchard and A. Heeger, April 21-25, 2003, San Francisco, CA.
211. **2003 Materials Research Society Spring Meeting,** "Effect of Illumination on Organic Polymer Thin-Film Transistors," M.C. Hamilton, S. Martin and J. Kanicki, April 21-25, 2003, San Francisco, CA.
212. **2003 Materials Research Society Spring Meeting,** "Source/Drain Contacts in Organic Polymer Thin Film Transistors," S. Martin, M. Hamilton and J. Kanicki, April 21-25, 2003, San Francisco, CA.
213. **Society for Information Display, 2003 Int. Symposium,** "200 dpi 3-a-Si:H TFTs Voltage-Driven AM-PLEDs," J.-H. Kim and J. Kanicki, May 21-22, 2003, Baltimore, MD.
214. **Society for Information Display, 2003 Int. Symposium,** "200 dpi 4-a-Si:H TFTs Current-Driven AM-PLEDs," Y. Hong, J.-Y. Nahm and J. Kanicki, May 21-22, 2003, Baltimore, MD.

215. **Society for Information Display, 2003 Int. Symposium**, “*Luminace Probes for contrast Measurements in Medical Displays,*” A. Badano, S. Pappada, E.F. Kelly, M.J. Flynn, S. Martin and J. Kanicki, May 21-22, 2003, Baltimore, MD.
216. **SPIE (The Int. Society for Optical Engineering) Meeting**, “*Organic Polymer Thin-Film Photo-Transistors,*” M.C. Hamilton, S. Martin and J. Kanicki, August 3-4, 2003, San Diego, CA.
217. **SPIE (The Int. Society for Optical Engineering) Meeting**, “*Time Dependence of Organic Polymer Thin-Film Transistors Current,*” S. Martin, L. Dassas, M.C. Hamilton and J. Kanicki, August 3-4, 2003, San Diego, CA.
218. **SPIE (The Int. Society for Optical Engineering) Meeting**, “*Influence of Gate Dielectric on the Electrical Properties of F8T2 Polyfluorene Thin-Film Transistors,*” J. Swensen, J. Kanicki and A.J. Heeger, August 3-4, 2003, San Diego, CA.
219. **SPIE (The Int. Society for Optical Engineering) Meeting**, “*Structural Ordering in F8T2 Polyfluorene Thin-Film Transistors,*” L. Kinder, J. Kanicki, J. Swensen and P. Petroff, August 3-4, 2003, San Diego, CA.
220. **23<sup>rd</sup> Int. Display Research Conf.**, “*Effect of Monochromatic Illumination on Organic Polymer Thin-Film Transistors,*” M.C. Hamilton, S. Martin and J. Kanicki, September 16-18, 2003, Phoenix, AZ.
221. **23<sup>rd</sup> Int. Display Research Conf.**, “*Electrical Instabilities of Organic Polymer Thin-Film Transistors,*” S. Martin, L. Dassas, M. Hamilton and J. Kanicki, September 16-18, 2003, Phoenix, AZ.
222. **23<sup>rd</sup> Int. Display Research Conf.**, “*Monte Carlo Simulations and Opto-Electronic Properties of Polymer Light-Emitting Devices on Flexible Plastic Substrates,*” S.J. Lee, A. Badano and J. Kanicki, September 16-18, 2003, Phoenix, AZ.
223. **Society of Information Display, 2005 Int. Symposium**, “*A Novel Current-Scaling a-Si:H TFTs Pixel Electrode Circuit for Active-Matrix Organic Light-Emitting Displays,*” Y.-C. Lin, H.-P. Shieh, C.-C. Su, H. Lee and J. Kanicki, May 24-27, 2005, Boston, MA.
224. **63<sup>rd</sup> Annual Device Research Conference**, “*Time and Temperature Dependence of the Drain Current of PF-based OFETs,*” M.C. Hamilton and J. Kanicki, June 20-22, 2005, Santa Barbara, CA.
225. **2005 Int. Conf. on Solid-State Devices and Materials**, “*White Light-Emitting Device on Flexible Plastic Substrates,*” H. Lee and J. Kanicki, September 13-15, 2005, Kobe, Japan.

226. **2005 MRS Fall Meeting**, “*Incorporating of Perovkite Oxides Into Gate Insulator of Zinc Oxide TFTs*,” J. Siddiqui, E. Cagin, P. Shea, J. Kanicki and J. Phillips, 2005, Boston, MA.
227. **Society for Information Display, 2006 Int. Symposium**, “*Current-Scaling a-Si:H TFT Pixel Electrode Circuit for AM-OLEDs*,” H. Lee, J. Kanicki, Y.C. Lin and H.-P. Shieh, June 7-9, 2006, San Francisco, CA.
228. **Electronic Materials Conf. 2006**, “*Zinc Tetrabenzoporphyrins Organic Field-Effect Transistors*,” P.B. Shea, J. Kanicki, M. Kawano, H. Yamada and N. Ono, June 28-30, 2006, State College, PA.
229. **13<sup>th</sup> Int. Workshop on “Active-Matrix Flat Panel Displays and Devices-TFT Technologies and Related Materials”**, *Novel Current-Scaling Current-Mirror a-Si:H TFT Pixel Electrode Circuit with Cascade Capacitor for AM-OLEDs*, H. Lee, J.-S. Yoo, C.-D. Kim, I.-J. Chung and J. Kanicki, July 5-7, 2006, Tokyo, Japan.
230. **Society for Information Display, 26<sup>th</sup> Int. Display Research Conference**, “*Reliability Enhancement of AM-OLED with a-Si:H TFT and Top-Anode OLED Employing a New Pixel Circuit*,” J.S. Yoo, H. Lee, J. Kanicki, C.-D. Kim and I.-J. Chung, September 18-21, 2006, Kent, OH.
231. **Society for Information Display, 2006 Vehicles and Photons Symposium**, “*White Light-Emitting Device on Flexible Plastic Substrate*,” H. Lee and J. Kanicki, October 12-13, 2006, Dearborn, MI.
232. **Society for Information Display, 2006 Vehicles and Photons Symposium**, “*Low Temperature Encapsulation for PLEDs and OLEDs*,” A.R. Johnson and J. Kanicki, October 12-13, 2006, Dearborn, MI.
233. **Society for Information Display, 2007 Vehicles and Photons Symposium**, “*Novel Pixel Electrode Circuits and a-Si:H TFT Structures for AM-OLEDs*,” H. Lee, J.S. Yoo, C.-D. Kim, I. Kang and J. Kanicki, October 11-12, 2007, Dearborn, MI.
234. **Society for Information Display, 2007 Vehicles and Photons Symposium**, “*Low Temperature Encapsulation for OLEDs*,” A.R. Johnson and J. Kanicki, October 11-12, 2007, Dearborn, MI.
235. **Society for Information Display, 2007 Vehicles and Photons Symposium**, “*Thermal and Electrical Instability of Amorphous Silicon Thin-Film Transistors for AM-FPDs*,” A. Kuo and J. Kanicki, October 11-12, 2007, Dearborn, MI.

236. **IDW '07 (The 14<sup>th</sup> International Display Workshop)**, "a-Si:H HEX-TFTs, a New Technology for Flat Panel Displays," H. Lee, J.S. Yoo, C.-D. Kim, I.B. Kang and J. Kanicki, December 5-7, 2007, Sapporo, Japan.
237. **Society for Information Display, 2008 Int. Symposium**, "Photosensitivity of Amorphous IGZO TFTs for Active-Matrix Flat-Panel Displays," C.-S. Chuang, T.-C. Fung, B. G. Mullins, K. Nomura, T. Kamiya, H.-P. D. Shieh, H. Hosono, and J. Kanicki, May 22, 2008, Los Angeles, California.
238. **66th Annual Device Research Conf.**, "Study of the Density of States of a-InGaZnO Using Field-Effect Technique," C. Chen, T.C. Fung, K. Abe, H. Kumomi and J. Kanicki, June 23-25, 2008, Santa Barbara, California.
239. **AM-FPD 08, The Fifteenth International Workshop on Active-Matrix Flatpanel Displays and Devices** "a-InGaZnO TFT Current-Scaling Pixel Electrode Circuit for AM-OLEDs," C. Chen, K. Abe, T.C. Fung, H. Kumomi, and J. Kanicki, July 2-4, 2008, Tokyo, Japan.
240. **AM-FPD 08, The Fifteenth International Workshop on Active-Matrix Flatpanel Displays and Devices**, "2-D Numerical Simulation of High Performance Amorphous In-Ga-Zn-O TFTs for Flat Panel Displays," T.C. Fung, C.S. Chuang, C. Chen, K. Abe, H. Kumomi and J. Kanicki, July 2-4, 2008, Tokyo, Japan.
241. **Society for Information Display—International Meeting (IMID 08, Digest of Technical Papers)**, "Photofield-Effect in Amorphous InGaZnO TFTs," T.-C. Fung, C.-S. Chuang, B. G. Mullins, K. Nomura, T. Kamiya, H.-P. D. Shieh, H. Hosono, and J. Kanicki, 2008.
242. **Society for Information Display, 2008 Vehicles and Photons Symposium**, "PLD Amorphous In-Ga-Zn-O TFTs for Future Optoelectronics," T.-C. Fung, K. Nomura, H. Hosono, and J. Kanicki, October 16-17, 2008, Dearborn, Michigan.
243. **Society for Information Display, 2008 Vehicles and Photons Symposium**, "RF Sputter a-InGaZnO Thin Film Transistors for Flat Panel Displays," C. Chen, K. Abe, H. Kumomi, J. Kumomi, and J. Kanicki, October 16-17, 2008, Dearborn, Michigan.
244. **The 28<sup>th</sup> International Display Research Conf.**, "Current Temperature Stress Study of RF Sputter a-InGaZnO TFTs," C. Chen, K. Abe, H. Kumomi, J. Kumomi, and J. Kanicki, November 4-6, 2008, Orlando, Florida.
245. **IDW '08 (The 15<sup>th</sup> International Display Workshop)**, "Bias-Temperature Stress Study of R.F. Sputter Amorphous In-Ga-Zn-O TFTs," T.-C. Fung, K. Abe, H. Kumomi and J. Kanicki," December 3-5, 2008, Niigata, Japan.

246. **SID (Society for Information Display), 2009 International Symposium**, “*DC / AC Electrical Instability of RF Sputter Amorphous In-Ga-Zn-O TFTs*,” T.-C. Fung, K. Abe, H. Kumomi and J. Kanicki, June 2-5, 2009, San Antonio, TX.
247. **SID (Society for Information Display), 2009 International Symposium**, “*AM-OLED Pixel Circuits Based on a-InGaZnO Thin Film Transistors*,” C. Chen, K. Abe, H. Kumomi and J. Kanicki, June 2-5, 2009, San Antonio, TX.
248. **29<sup>th</sup> International Display Research Conference, EuroDisplay 2009**, “*A Maskless Laser-Write Lithography Processing of Thin-Film Transistors*,” G. Yoo, W. Salewski, J. Herrmann and J. Kanicki September 14-17, 2009, Rome, Italy.
249. **29<sup>th</sup> International Display Research Conference, EuroDisplay 2009**, “*Electrical Stability of Hexagonal a-Si:H TFTs*,” G. Yoo, H. Lee and J. Kanicki, September 14-17, 2009, Rome, Italy.
250. **6<sup>th</sup> International Thin – Film Transistor Conference**, “*Threshold Voltage Control of the D.C. Sputtered Staggered Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistor*,” A. Kuo, K. Abe, H. Kunomi, and J. Kanicki, January 28 – 29, 2010, Egret, Himeji, Japan
251. **SID (Society for Information Display), 2011 International Symposium**, , “*Electrical Properties and Stability of Dual-Gate Coplanar Homojunction Amorphous Indium-Gallium-zinc-Oxide Thin – Film Transistor*,” G. Baek, A. Kuo, K. Abe, H. Kumomi and J. Kanicki, May 17 - 20, 2011, Los Angeles, CA
252. **SID (Society for Information Display), 2011 Vehicles and Photons Symposium**, “*Analytical Models of Synchronized Dual-Gate a-IGZO TFTs*,” G. Baek and J. Kanicki, October 20 – 21, 2011, Dearborn, MI